
2SJ351, 2SJ352

Silicon P-Channel MOS FET

HITACHI

ADE-208-143
1st. Edition

Application

Low frequency power amplifier

Complementary pair with 2SK2220, 2SK2221

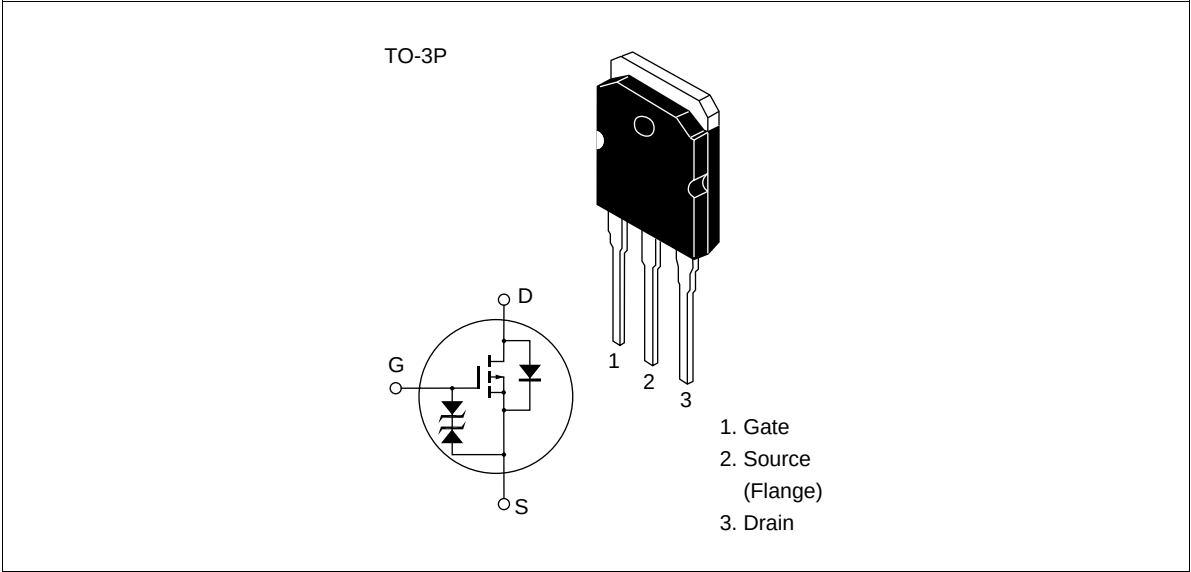
Features

- High power gain
- Excellent frequency response
- High speed switching
- Wide area of safe operation
- Enhancement-mode
- Good complementary characteristics
- Equipped with gate protection diodes

Ordering Information

Type No.	V_{DSX}
2SJ351	–180 V
2SJ352	–200 V

Outline



Absolute Maximum Ratings (Ta = 25°C)

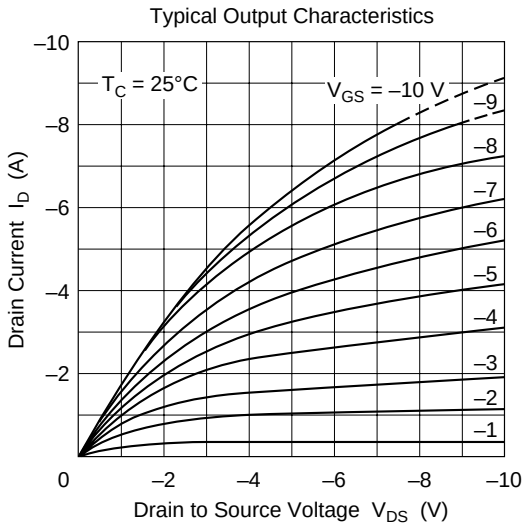
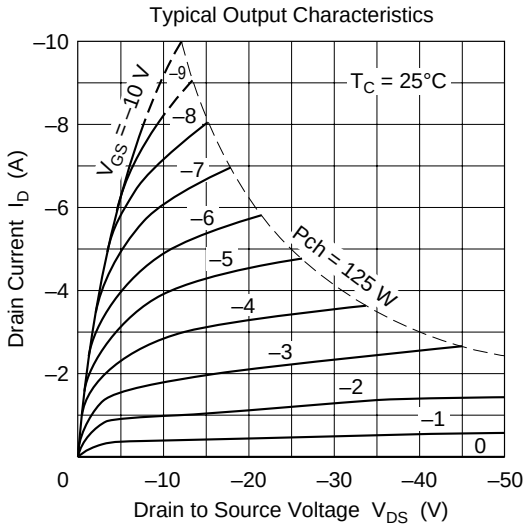
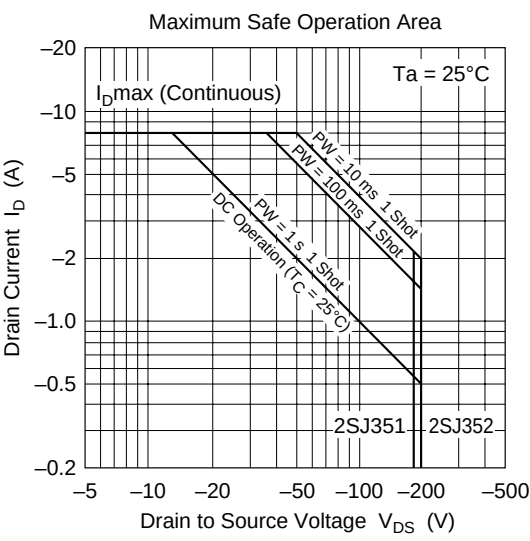
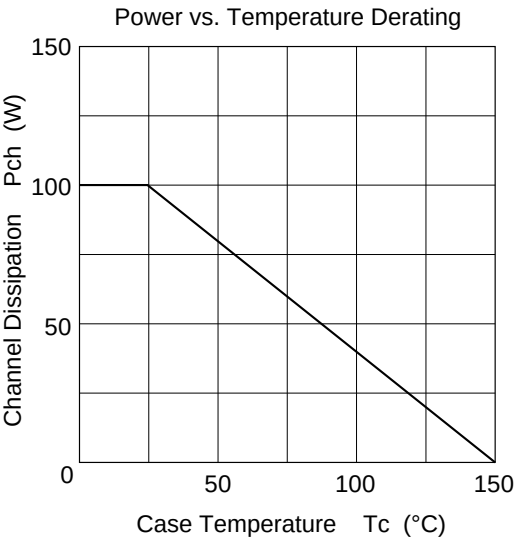
Item		Symbol	Ratings	Unit
Drain to source voltage	2SJ351	V_{DSX}	-180	V
	2SJ352		-200	
Gate to source voltage		V_{GSS}	±20	V
Drain current		I_D	-8	A
Body to drain diode reverse drain current		I_{DR}	-8	A
Channel dissipation		P_{ch}^{*1}	100	W
Channel temperature		T_{ch}	150	°C
Storage temperature		T_{stg}	-55 to +150	°C

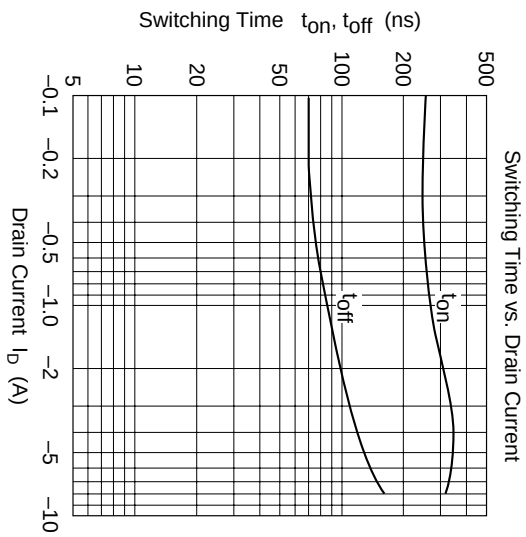
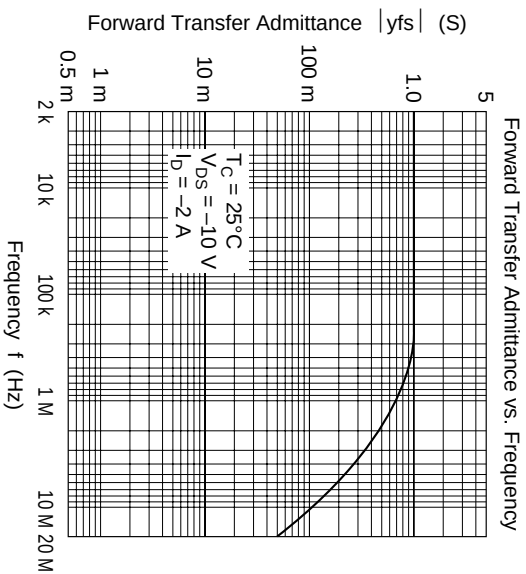
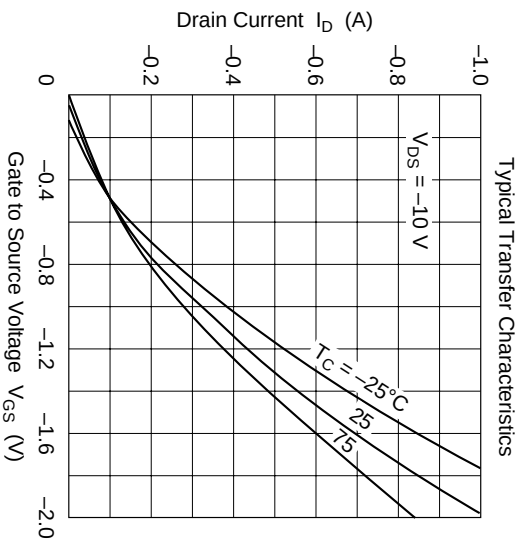
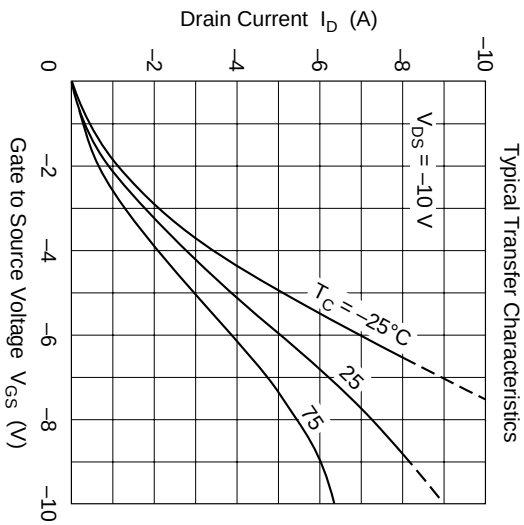
Note: 1. Value at $T_c = 25^\circ\text{C}$

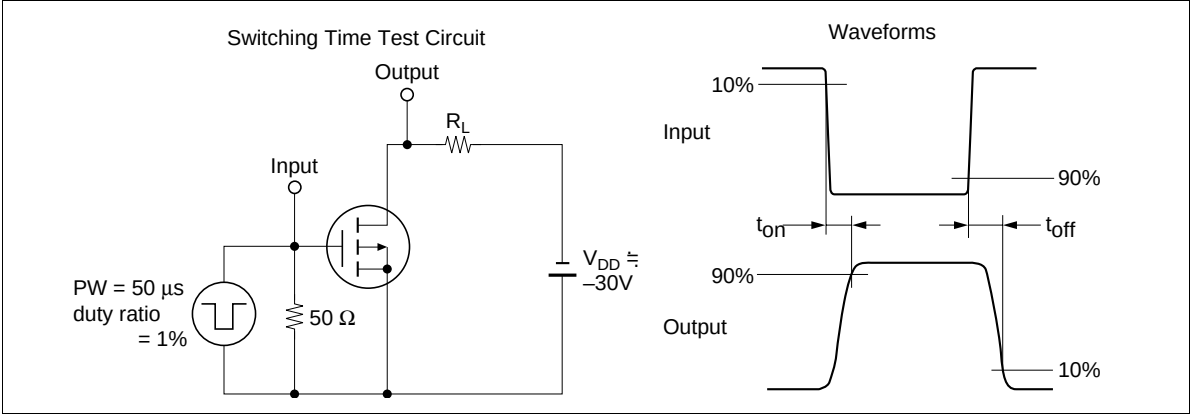
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	2SJ351 2SJ352	$V_{(BR)DSX}$	-180 -200	— —	— —	V	$I_D = -10\text{ mA}$, $V_{GS} = 10\text{ V}$
Gate to source breakdown voltage		$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100\text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	-0.15	—	-1.45	V	$I_D = -100\text{ mA}$, $V_{DS} = -10\text{ V}$
Drain to source saturation voltage		$V_{DS(sat)}$	—	—	-12	V	$I_D = -8\text{ A}$, $V_{GD} = 0^{*1}$
Forward transfer admittance		$ y_{fs} $	0.7	1.0	1.4	S	$I_D = -3\text{ A}$, $V_{DS} = -10\text{ V}^{*1}$
Input capacitance		C_{iss}	—	800	—	pF	$V_{GS} = 5\text{ V}$, $V_{DS} = -10\text{ V}$, $f = 1\text{ MHz}$
Output capacitance		C_{oss}	—	1000	—	pF	
Reverse transfer capacitance		C_{rss}	—	18	—	pF	
Turn-on time		t_{on}	—	320	—	ns	$V_{DD} = -30\text{ V}$, $I_D = -4\text{ A}$
Turn-off time		t_{off}	—	120	—	ns	

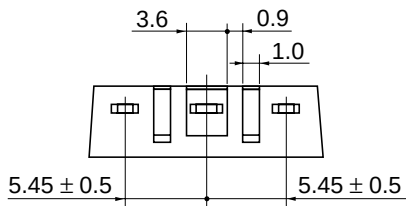
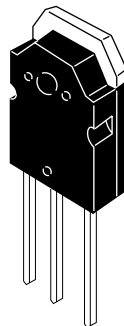
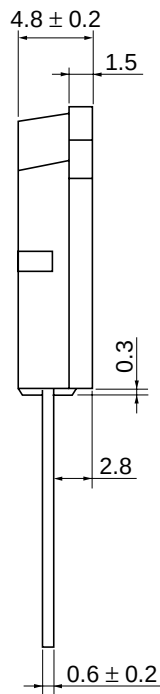
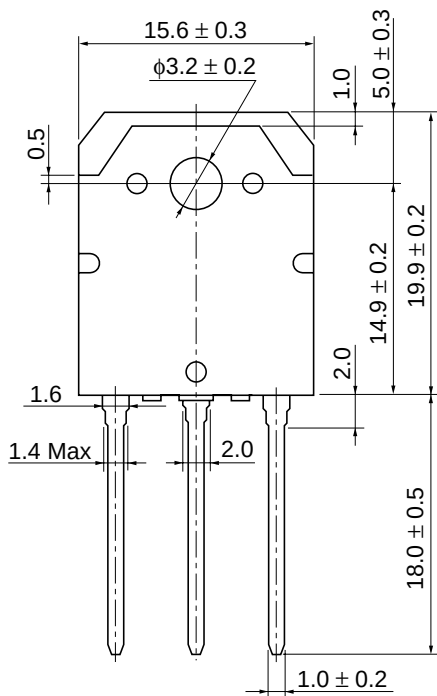
Note: 1. Pulse test







Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Weight (reference value)	5.0 g

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